25C1226, 25C1226A

Silicon NPN Epitaxial Planar Type

Medium Power Amplifier Complementary Pair with 2SA699, 2SA699A

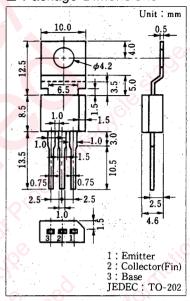
■ Feature

• 5W output in complementary pair with 2SA699, 2SA699A

■ Absolute Maximum Ratings (Ta=25°C)

Item		Symbol	Value	Unit	
Collector-	2SC1226	V	40	V	
base voltage	2SC1226A	V _{Сво}	50	V	
Collector- emitter voltage	2SC1226		32	V	
	2SC1226A	V_{CEO}	40	v	
Emitter-base voltage		VEBO	5	V	
Peak collector current		Icr	3	A	
Base current		I_{B}	0.6	A	
Collector power dissipation (Tc=25°C)		Pc	10	W	
Junction temperature		T_{i}	150	°C	
Storage temperature		Tstg	$-55 \sim +150$. ℃	
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■ Package Dimensions



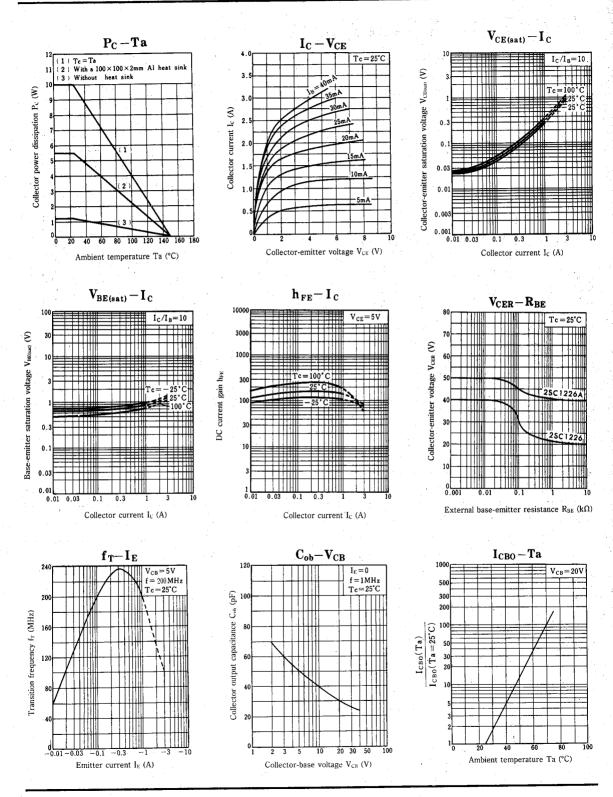
■ Electrical Characteristics (Tc=25°C)

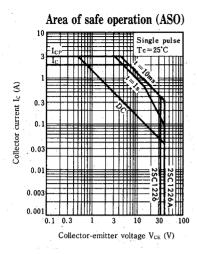
Item	Symbol	Condition	min.	typ.	max.	Unit
	Ісво	$V_{CB} = 20 \text{ V}, I_{E} = 0$			1	μA
Collector cutoff current	I _{CEO}	$V_{CE} = 12 \text{ V}, I_{B} = 0$			100	μΑ
Emitter cutoff current	I _{EBO}	$V_{EB} = 5 \text{ V}, I_{C} = 0$	9		100	μΑ
Collector- 2SC1226	$V_{\sf CBO}$	$I_{\rm C}=1$ mA, $I_{\rm F}=0$	40		5	v
base voltage 2SC1226A	V CBO	ic-ima, ie-o	50	4		
Collector- 2SC1226	V _{CEO}	$I_C = 10 \text{ mA}, I_B = 0$. 32			V
emitter voltage 2SC1226A			40			
DC current gain	h _{FE} *1	$V_{CE} = 5V, I_{C} = 1 A^{*2}$	50	120	220	
Transition frequency	f_T	$V_{CE} = 5 V, I_C = 0.5 A^{*2}$		(150)		MHz
Base-emitter saturation voltage	V _{BE(sat)}	$I_C=2 A, I_B=0.2 A^{*2}$	1		1.5	V
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C=2 A, I_B=0.2 A^{*2}$		0.4	1	V
Collector output capacitance	Сов	$V_{CB} = 5 V$, $I_{E} = 0$, $f = 1 MHz$	3	50	,	pF

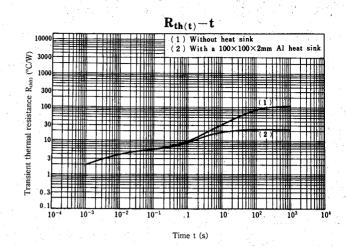
*hFE Classifications

Class	P	Q	R
h_{FE}	50~100	80~160	120~220

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